

# Bias Resistor Transistor

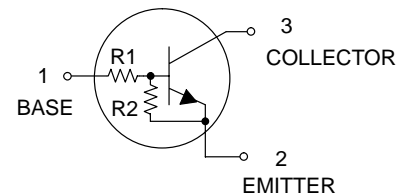
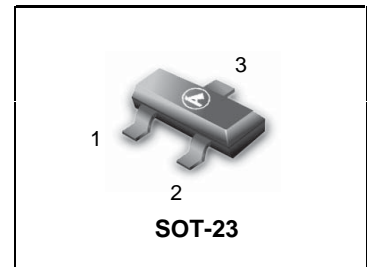
## NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

**LDTC144GLT1G**

- **Applications**  
Inverter, Interface, Driver

- **Features**
  - 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
  - 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
  - 3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.



### ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>c</sub>	100	mA
Collector Power dissipation	DTC144GE	150	mW
	DTC144GUA / DTC144GKA	200	
	DTC144GSA	300	
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTC144GLT1G	L1	-	47	3000/Tape & Reel
LDTC144GLT3G	L1	-	47	10000/Tape & Reel

### ● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	50	-	-	V	I <sub>c</sub> =50μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	50	-	-	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	5	-	-	V	I <sub>E</sub> =160μA
Collector cutoff current	I <sub>CB0</sub>	-	-	0.5	μA	V <sub>CB</sub> =50V
Emitter cutoff current	I <sub>EBO</sub>	65	-	130	μA	V <sub>EB</sub> =4V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	-	0.3	V	I <sub>c</sub> =10mA, I <sub>B</sub> =0.5mA
DC current transfer ratio	h <sub>FE</sub>	68	-	-	-	I <sub>c</sub> =5mA, V <sub>CE</sub> =5V
Emitter-base resistance	R	32.9	47	61.1	kΩ	-
Transition frequency	f <sub>t</sub>	-	250	-	MHz	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz *

\* Transition frequency of the device.

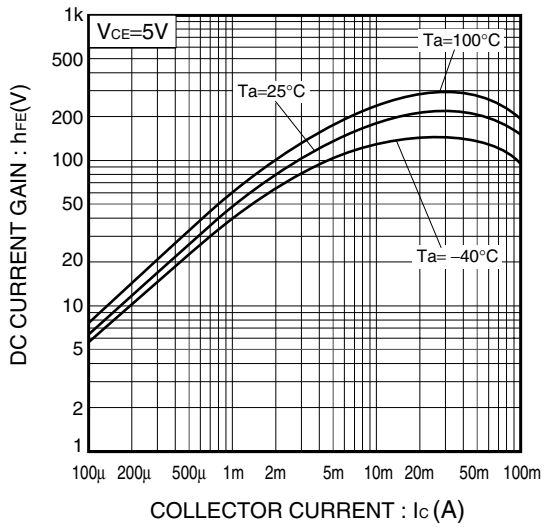
**LDTC144GLT1G**
**●Electrical characteristic curves**


Fig.1 DC current gain vs. Collector current

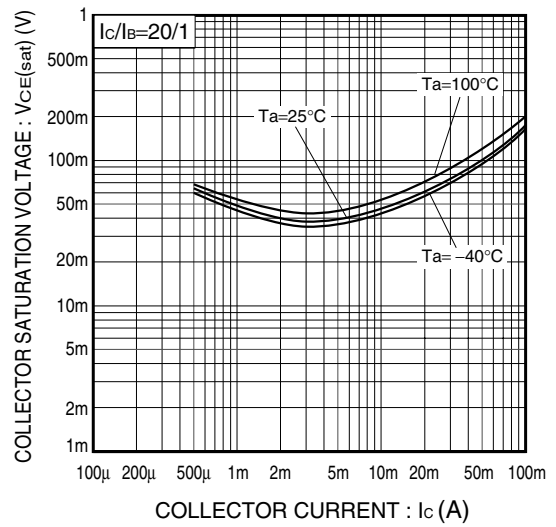


Fig.2 Collector-Emmitter saturation voltage vs. Collector current

**LDTC144GLT1G**

**SOT-23**

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

